

Amel reacting the alkylsilane in the presence of the plasma to form silicon carbide;
depositing a metal barrier layer on the silicon carbide barrier layer; and
depositing a metal layer over the metal barrier layer.

2. The method of claim 1, wherein the alkylsilane comprises a methyl group.
3. The method of claim 1, wherein the alkylsilane is trimethylsilane.
4. The method of claim 1, wherein the silicon carbide barrier layer is deposited at a temperature of between about 100°C to about 450°C.
5. The method of claim 1, wherein the silicon carbide barrier layer is deposited at a temperature of between about 300°C to about 400°C.
6. The method of claim 1, wherein the silicon carbide barrier layer has a dielectric constant of about 6 or less.
7. The method of claim 1, wherein the silicon carbide barrier layer has a dielectric constant of about 3 or less.
8. The method of claim 1, further comprising depositing a second silicon carbide barrier layer on the metal layer.
10. The method of claim 1, wherein the silicon carbide barrier layer is deposited at a chamber pressure between about 6 to about 10 Torr.
11. The method of claim 1, wherein the silicon carbide barrier layer is deposited using an RF power supply supplying a power density of about 4.3 to about 10.0 watts per square inch to an anode and cathode in the chamber.

12. The method of claim 1, wherein the silicon carbide barrier layer is deposited with an alkylsilane flow rate of between about 10 to about 1000 sccm and a helium or argon flow rate of between about 50 to about 5000 sccm.

13. The method of claim 1, wherein the silicon carbide barrier layer is deposited with a methylsilane flow rate of between about 30 to about 500 sccm, a helium or argon gas flow rate of between about 100 to about 2000 sccm, a chamber pressure of about 3 to about 10 Torr, an RF power source supplying a power density of about 4.3 to about 10.0 watts per square inch to an anode and cathode in the chamber, a substrate surface temperature of between about 200°C to about 400°C, and a showerhead to substrate surface spacing of between about 300 to about 600 mils.

15. (Twice Amended) The method for processing a substrate, comprising:
depositing a silicon carbide barrier layer on the substrate by a method comprising:

introducing an alkylsilane and a noble gas into a chamber;
initiating a plasma in the chamber; and
reacting the alkylsilane in the presence of the plasma to form silicon

carbide;

depositing a first dielectric layer on the silicon carbide layer;

depositing a silicon carbide etch stop having an etch selectivity ratio of at least about 40 to 1 on the first dielectric layer by a method comprising:

introducing an alkylsilane and a noble gas into a chamber;

initiating a plasma in the chamber; and

reacting the alkylsilane in the presence of the plasma to form silicon carbide;

patternning the silicon carbide etch stop;

depositing a second dielectric layer on the silicon carbide etch stop;

etching the first dielectric layer and the second dielectric layer to form a feature definition;

depositing a tantalum nitride barrier layer in the feature definition;

Page 3

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depositing a copper layer over the tantalum nitride layer to fill the feature definition; and

depositing a silicon carbide passivation layer on the copper layer.

16. The method of claim 15, wherein the alkylsilane is trimethylsilane.
17. The method of claim 15, wherein the silicon carbide barrier layer is deposited at a temperature of between about 300°C to about 400°C.
18. The method of claim 15, wherein the silicon carbide barrier layer is deposited at a chamber pressure between about 6 to about 8 Torr.
19. The method of claim 15, wherein the silicon carbide passivation layer is deposited by the method for depositing the silicon carbide barrier layer.
20. The method of claim 15, wherein the silicon carbide barrier layer is deposited using an RF power supply supplying a power density of about 8.6 to about 14.3 watts per square inch to an anode and cathode in the chamber.
21. The method of claim 15, wherein the silicon carbide barrier layer is deposited with a methylsilane flow rate of between about 100 to about 500 sccm, a helium or argon gas flow rate of between about 1000 to about 2000 sccm, a chamber pressure of about 6 to about 8 Torr, an RF power source supplying a power density of about 8.6 to about 14.3 watts per square inch to an anode and cathode in the chamber, a substrate surface temperature of between about 200°C to about 400°C, and a showerhead to substrate surface spacing of between about 300 to about 600 mils.
22. The method of claim 15, wherein the alkylsilane is derived from a common methylsilane selected from the group of methylsilane, dimethylsilane, trimethylsilane, and combinations thereof.

23. (Cancelled) A substrate having a silicon carbide layer deposited thereon, comprising:

- a substrate;
- a dielectric layer deposited on the substrate;
- a silicon carbide layer deposited on the dielectric layer and having a dielectric constant of about 6 or less;
- a metal barrier layer deposited on the silicon carbide layer; and
- a metal layer deposited on the metal barrier layer.

24. (Cancelled) The substrate of claim 23, wherein the silicon carbide layer has a dielectric constant of about 3 or less.

25. (Cancelled) The substrate of claim 23, wherein the metal barrier layer comprises tantalum, tantalum nitride, or combinations thereof.

26. (Cancelled) The substrate of claim 23, wherein the metal layer comprises copper.

27. (Cancelled) The substrate of claim 23, wherein the silicon carbide layer is produced by the process of providing a methylsilane flow rate of between about 30 to about 500 sccm, a helium or argon gas flow rate of between about 100 to about 2000 sccm, a chamber pressure of about 3 to about 10 Torr, an RF power source supplying a power density of about 4.3 to about 10.0 watts per square inch to an anode and cathode in the chamber, a substrate surface temperature of between about 200°C to about 400°C, and a showerhead to substrate surface spacing of between about 300 to about 600 mils.